



MMBT5401LT1

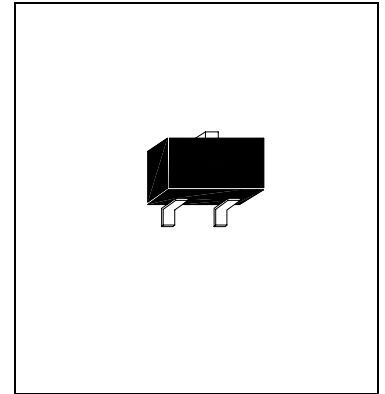
PNP EPITAXIAL PLANAR TRANSISTOR

Description

The MMBT5401LT1 is designed for general purpose applications requiring high breakdown voltages.

Features

- High Collector-Emitter Breakdown Voltage. $BV_{CEO}=150V$ (@ $I_C=1mA$)
- Complements to NPN Type MMBT5551LT1.



Absolute Maximum Ratings

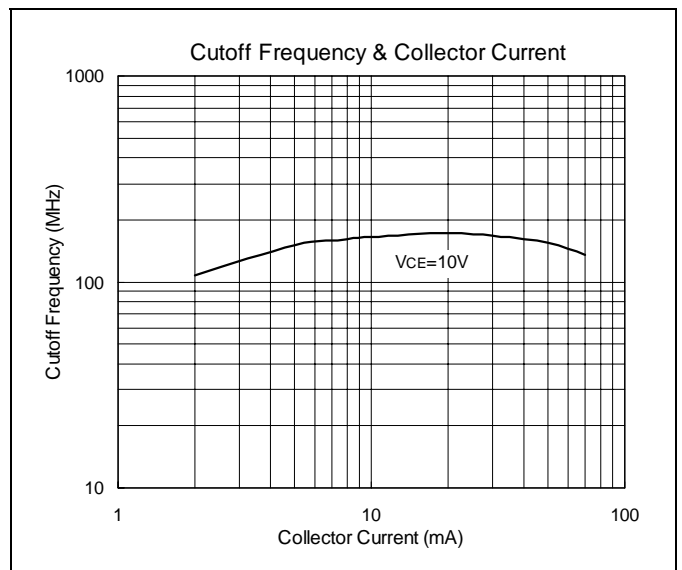
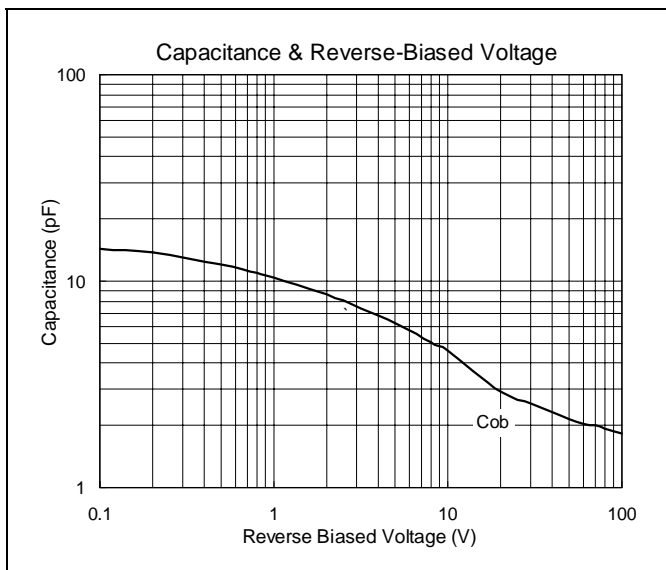
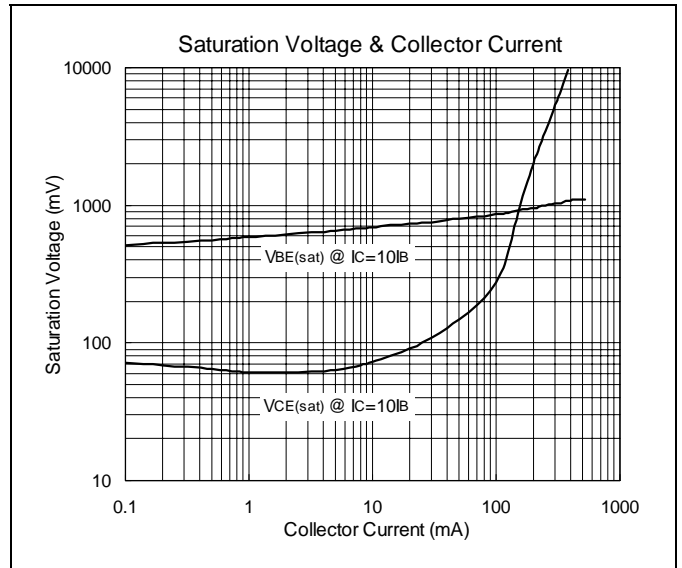
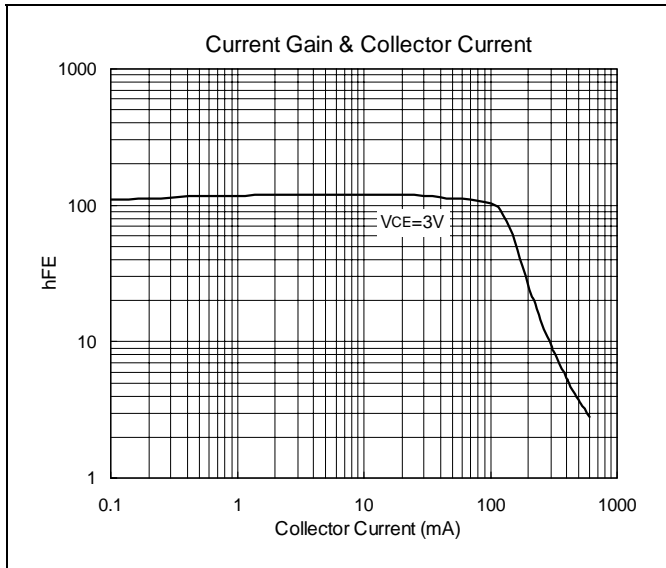
- Maximum Temperatures
Storage Temperature -55~+150 °C
Junction Temperature +150°C Maximum
- Maximum Power Dissipation
Total Power Dissipation ($T_a=25^{\circ}C$) 250 mW
- Maximum Voltages and Currents ($T_a=25^{\circ}C$)
VCBO Collector to Base Voltage 160 V
VCEO Collector to Emitter Voltage 150 V
VEBO Emitter to Base Voltage 5 V
IC Collector Current 500mA

Characteristics ($T_a=25^{\circ}C$)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	160	-	-	V	$I_C=100\mu A$
BVCEO	150	-	-	V	$I_C=1mA$
BVEBO	5	-	-	V	$I_E=10\mu A$
ICBO	-	-	50	nA	$V_{CB}=120V$
VCE(sat)1	-	-	200	mV	$I_C=10mA, I_B=1mA$
VCE(sat)2	-	-	500	mV	$I_C=50mA, I_B=5mA$
VBE(sat)1	-	-	1	V	$I_C=10mA, I_B=1mA$
VBE(sat)2	-	-	1	V	$I_C=50mA, I_B=5mA$
hFE1	50	-	-		$V_{CE}=5V, I_C=1mA$
hFE2	60	-	240		$V_{CE}=5V, I_C=10mA$
hFE3	50	-	-		$V_{CE}=5V, I_C=50mA$
fT	100	-	300	MHz	$V_{CE}=10V, I_C=10mA, f=100MHz$
Cob	-	-	6	pF	$V_{CB}=10V, f=1MHz$

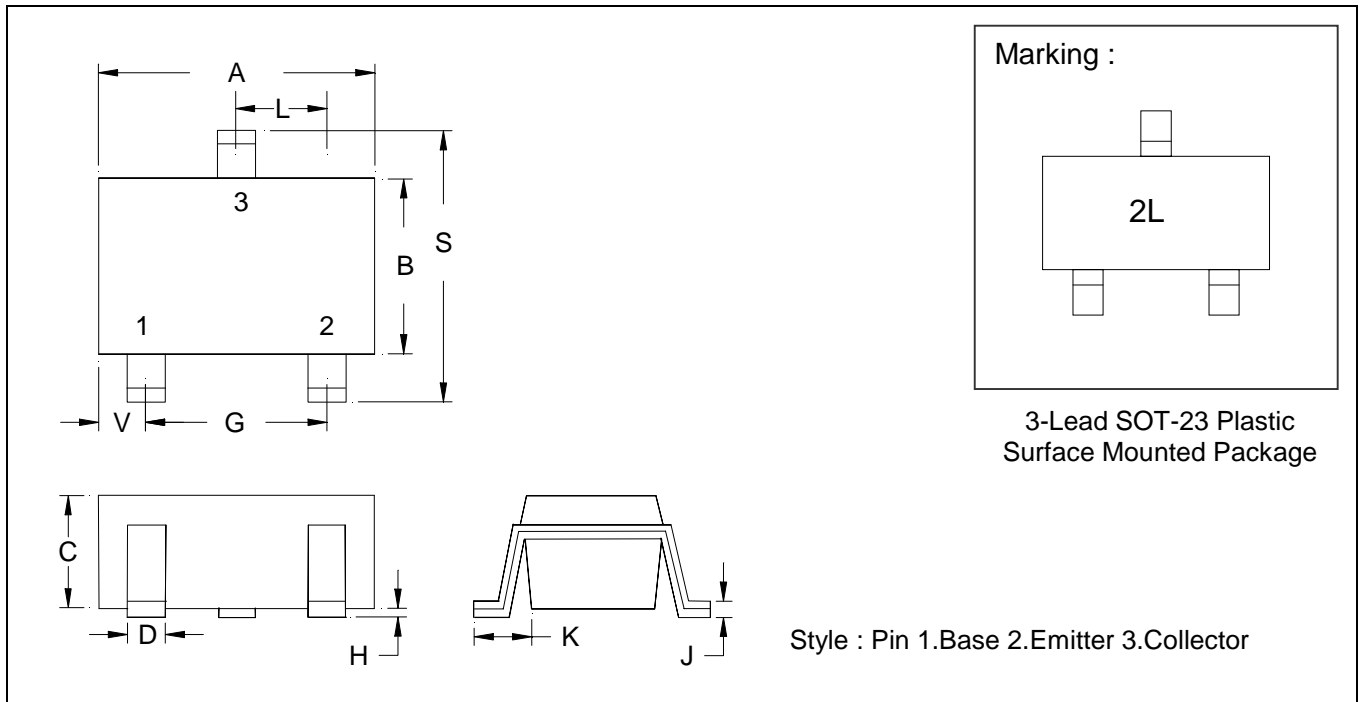


Characteristics Curve





SOT-23 Dimension



*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.118	2.80	3.00	J	0.0035	0.0043	0.09	0.11
B	0.0550	0.0630	1.40	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0354	0.0512	0.90	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0886	0.1083	2.25	2.75
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	-	0.0040	-	0.10					